

.025" NPN Phototransistors

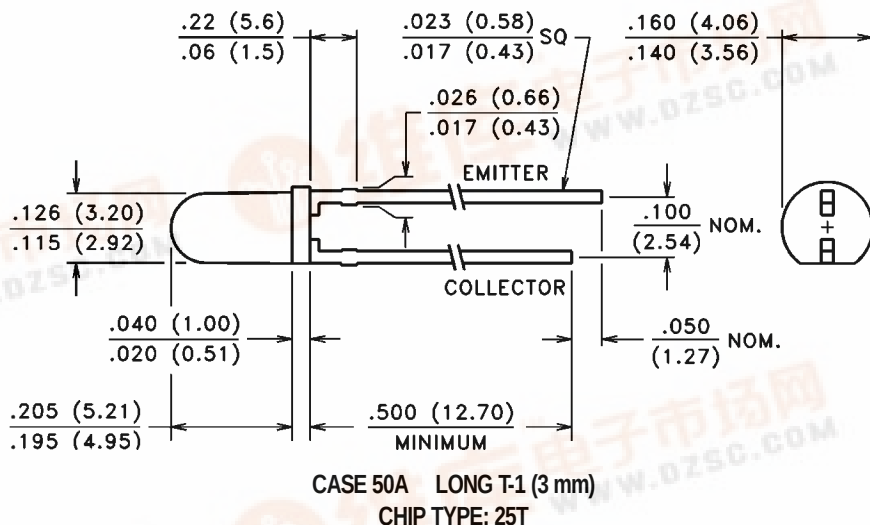
IRT Long T-1 (3 mm) Plastic Package

捷多邦, 专业PCB打样工厂, 24小时加急出货

VTT3423LA, 4LA, 5LA



PACKAGE DIMENSIONS inch (mm)



PRODUCT DESCRIPTION

A small area high speed NPN silicon phototransistor in a 3 mm diameter, lensed plastic package. The package material transmits infrared and blocks visible light. These devices are spectrally and mechanically matched to the VTE33xxLA series of IREDs.

ABSOLUTE MAXIMUM RATINGS ■

(@ 25°C unless otherwise noted)

Maximum Temperatures	
Storage Temperature:	-40°C to 100°C
Operating Temperature:	-40°C to 100°C
Continuous Power Dissipation:	50 mW
Derate above 30°C:	0.71 mW/°C
Maximum Current:	25 mA
Lead Soldering Temperature:	260°C
(1.6 mm from case, 5 sec. max.)	

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also typical curves, pages 91-92)

Part Number ■	Light Current			Dark Current		Collector Breakdown	Emitter Breakdown	Saturation Voltage	Rise/Fall Time	Angular Response $\theta_{1/2}$
	I_C			I_{CEO}		$V_{BR(CEO)}$	$V_{BR(EO)}$	$V_{CE(SAT)}$	t_R/t_F	
	mA		H fc (mW/cm ²) $V_{CE} = 5.0\text{ V}$	$H = 0$		$I_C = 100\text{ }\mu\text{A}$ $H = 0$	$I_E = 100\text{ }\mu\text{A}$ $H = 0$	$I_C = 1.0\text{ mA}$ $H = 400\text{ fc}$	$I_C = 1.0\text{ mA}$ $R_L = 100\text{ }\Omega$	
	Min.	Max.		(nA) Max.	V_{CE} (Volts)	Volts, Min.	Volts, Min.	Volts, Max.	$\mu\text{sec, Typ.}$	Typ.
VTT3423LA	1.0	—	20 (1)	100	10	30	5.0	0.25	3.0	$\pm 10^\circ$
VTT3424LA	2.0	—	20 (1)	100	10	30	5.0	0.25	4.0	$\pm 10^\circ$
VTT3425LA	3.0	—	20 (1)	100	10	30	5.0	0.25	5.0	$\pm 10^\circ$

Refer to General Product Notes, page 2.

